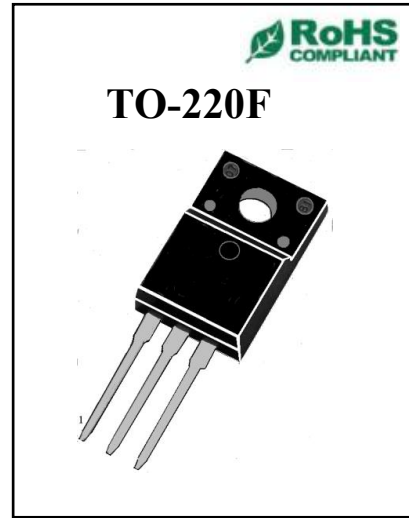


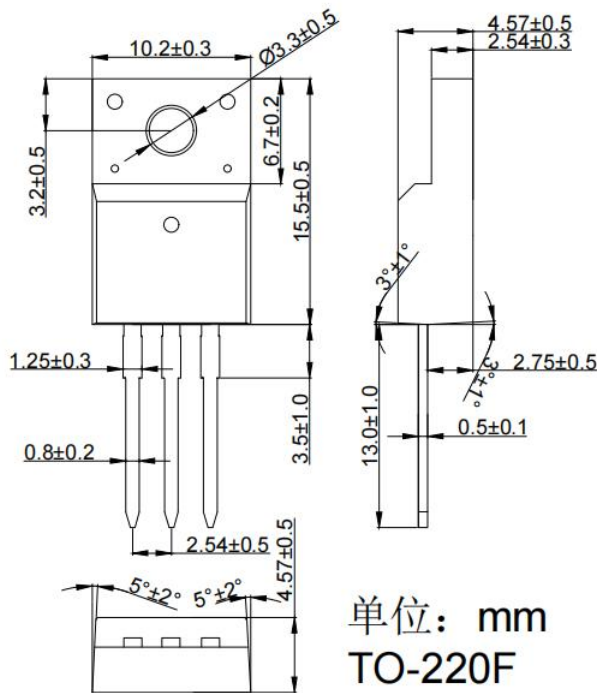
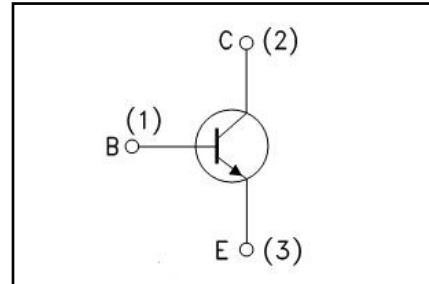
◆ **Features:**

- ◇ High efficiency, low deviation
高效率, 低偏差
- ◇ Small input impedance, low consumption of power
输入阻抗小, 功耗低
- ◇ Resistant of high temperature, high humidity
抗高温、高湿
- ◇ Good stability, reliability
稳定性好, 可靠性高



◆ **Applications**

- ◇ Power amplifier applications
功率放大器应用
- ◇ Driver stage amplifier applications
驱动级放大器的应用
- ◇ Complement to Type A1837(PNP)
与 A1837 互补应用





2SC4793/2SA1837

NPN/PNP Complementary Silicon Power Transistors

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	230	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	230	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	5	V
Ic	Collector Current-Continuous 集电极连续电流	1	A
I _B	Base Current-Continuous 基极连续电流	0.1	A
PC	Collector Power Dissipation 耗散功率	20	W
T _j	Max.Operating junction temperature 最大结温	150	°C
Tstg	Storage Temperature 存储温度	-55 ~ +125	°C

unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I _{CBO}	Collector Cutoff Current 集电极截止电流		--	1	μA	V _{CE} =230V, I _B =0
I _{EBO}	Emitter Cutoff Current 发射极截止电流		--	1	μA	V _{EB} =5V, I _C =0
BV _{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	230			V	I _C =10mA, I _B =0
V _{CE(sat)}	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压			1.4	V	I _C =5A, I _B =0.5A
h _{FE}	DC Current Gain(Note 1) 直流电流增益	100	--	320		I _C =1A, V _{CE} =5V
f _T	Current-Gain—Bandwidth 电流增益带宽	100	--	--	MHZ	V _{CE} =10V, I _C =0.1A

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.